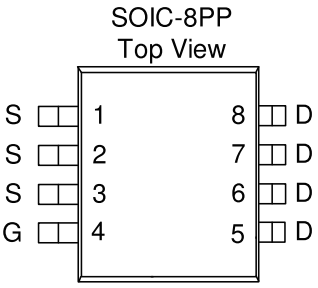
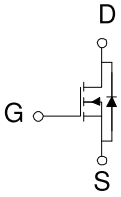
N-Channel 80-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
80	11 @ V_{GS} = 10V	18
	13 @ V_{GS} = 4.5V	17

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8PP saves board space
- Fast switching speed
- High performance trench technology





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	20	
Continuous Drain Current[a]	T_A=25°C	I_D	18	A
	T_A=70°C		15	
Pulsed Drain Current[b]		I_{DM}	50	
Continuous Source Current (Diode Conduction)[a]		I_S	2.3	A
Power Dissipation[a]	T_A=25°C	P_D	5.0	W
	T_A=70°C		3.2	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient[a]	t <= 10 sec	$R_{\theta JA}$	25	°C/W
	Steady State		65	°C/W

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

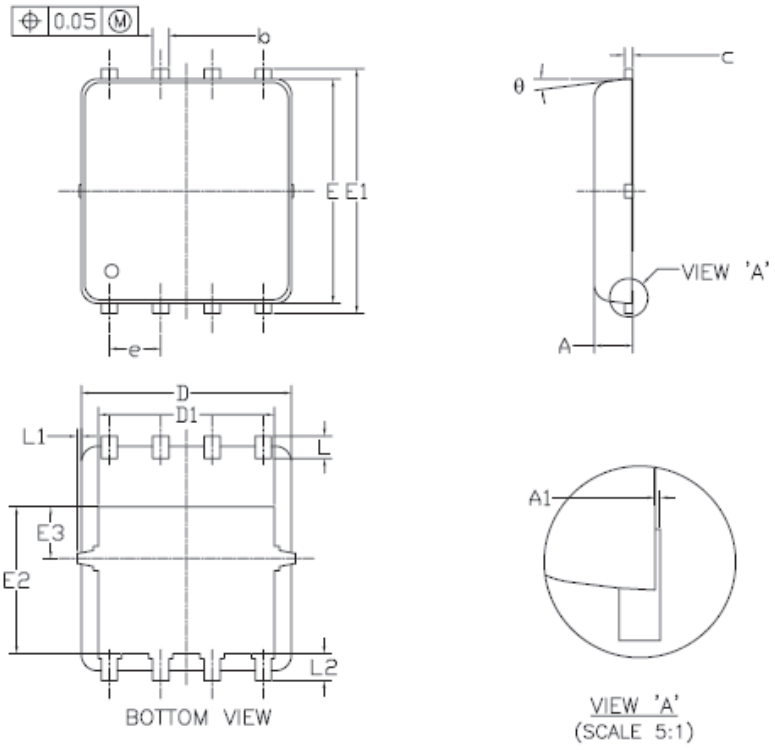
SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	1			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = 12 V			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 64 V, V_{GS} = 0 V			1	uA
		V_{DS} = 64 V, V_{GS} = 0 V, T_J = 55°C			5	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	40			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 2 A			11	mΩ
		V_{GS} = 4.5 V, I_D = 2 A			13	
Forward Tranconductance[A]	g_{fs}	V_{DS} = 15 V, I_D = 6 A		40		S
Diode Forward Voltage	V_{SD}	I_S = 2.3 A, V_{GS} = 0 V		0.7		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 6 A		60		nC
Gate-Source Charge	Q_{gs}			20		
Gate-Drain Charge	Q_{gd}			30		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 6 Ω , ID = 1 A, VGEN = 10 V		17		nS
Rise Time	t_r			50		
Turn-Off Delay Time	$t_{d(off)}$			200		
Fall-Time	t_f			70		

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	——	0.05	0.000	——	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.20 BSC			0.205 BSC		
D1	4.35 BSC			0.171 BSC		
E	5.55 BSC			0.219 BSC		
E1	6.05 BSC			0.238 BSC		
E2	3.625 BSC			0.143 BSC		
E3	1.275 BSC			0.050 BSC		
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	——	0.15	0	——	0.006
L2	0.68 REF			0.027 REF		
θ	0°	——	10°	0°	——	10°